

# MAC15 Series



## Description

Designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

## Features

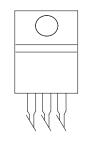
- Blocking Voltage to 800 V
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC15 Series) or Four Modes (MAC15A Series)

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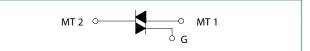
• These Devices are Pb–Free and are RoHS Compliant

## Pin Out





## **Functional Diagram**



## **Additional Information**







Samples

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## **Maximum Ratings** (T<sub>1</sub> = 25°C unless otherwise noted)

, v			
Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1)       MAC15A60         (Gate Open, Sine Wave 50 to 60 Hz, T <sub>J</sub> = 25° to 100°C)       MAC15-8G, MAC15A80	B V <sub>DRM</sub> ,	400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 50 to 60 Hz, $T_c = 90^{\circ}$ C)	I <sub>T (RMS)</sub>	15	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_J$ = 125°C) Preceded and Followed by Rated Current	I <sub>TSM</sub>	150	А
Peak Gate Voltage (Pulse Width ::: 1.0 μsec; TC = 90°C)	V <sub>GM</sub>	10	V
Circuit Fusing Consideration (t = 8.3 ms)	l²t	93	A <sup>2</sup> sec
Peak Gate Power ( $T_c = +80^{\circ}C$ , Pulse Width = 1.0 µs)	P <sub>GM</sub>	20	W
Peak Gate Current (Pulse Width ::: 1.0 µsec; TC = 90°C)	I <sub>GM</sub>	2.0	А
Average Gate Power (t = 8.3 ms, $T_c = 80^{\circ}$ C)	P <sub>G (AV)</sub>	0.5	W
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thermal Characteristics						
Rating		Symbol	Value	Unit		
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.0 62.5	°C/W		
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		TL	260	°C		

## **Electrical Characteristics** OFF $(T_1 = 25^{\circ}C \text{ unless otherwise noted}; Electricals apply in both directions)$

Characteristic		Symbol	Min	Тур	Мах	Unit
Peak Repetitive Blocking Current	T <sub>1</sub> = 25°C	I <sub>DRM</sub> ,	-	-	1.0	m ^
$(V_{D} = V_{DRM} = V_{RRM}; \text{ Gate Open})$	T_ = 125°C	I	-	-	2.0	mA

#### **Electrical Characteristics** • **ON** (T = 25°C unless otherwise noted; Electricals apply in both directions)

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Characteristic			Min	Тур	Мах	Unit
Peak On–State Voltage (Note 2) (I <sub>TM</sub> = ±21 A Peak)		V <sub>TM</sub>	-	1.3	1.6	V
	MT2(+), G(+)		_	_	50	
Gate Trigger Current	MT2(+), G(-)		_	_	50	
(Continuous dc) ( $V_p = 12 V, R_1 = 100 \Omega$ )	MT2(-), G(-)	GT	_	_	50	mA
$v_{\rm D} = 12 v_{\rm r} n_{\rm L} = 100 227$	MT2(-), G(+)				75	
	MT2(+), G(+)		0.5	0.62	1.3	
Gate Trigger Voltage	MT2(+), G(-)	V <sub>gt</sub>	0.5	0.57	1.3	
(Continuous dc) ( $V_{p} = 12 V, R_{1} = 100 \Omega$ )	MT2(-), G(-)		0.5	0.65	1.3	V
$(v_D - 12, v_1, 11_2 - 100, 22)$	MT2(-), G(+)		0.5	0.74	1.3	
	MT2(+), G(+)		0.2	-	-	
Gate Non-Trigger Voltage ( $T_{_J} = 125^{\circ}C$ ) ( $V_{_{D}} = 12 V$ , $R_{_{_{J}}} = 100 \Omega$ )	MT2(+), G(-)		0.2	-	-	
	MT2(-), G(-)	- V <sub>gd</sub>	0.2	-	-	- V
	MT2(), G(+)		0.2	-	-	
Holding Current ( $V_p = 12 V_{dc}$ , Gate Open, Initiating Current = ±200 mA))		I <sub>H</sub>	-	6.0	40	mA

2. Indicates Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%.

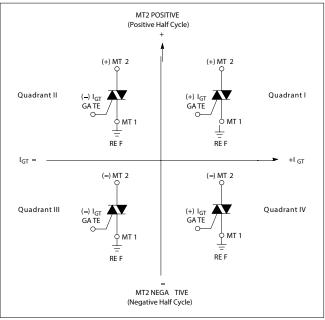


Dynamic Characteristics						
Characteristic	Symbol	Min	Тур	Max	Unit	
Critical Rate of Rise of Commutation Voltage (V <sub>D</sub> = Rated V <sub>DRM</sub> , I <sub>TM</sub> = 21 A, Commutating di/dt = 7.6 A/ms, Gate Unenergized, TC = 80°C)	dV/dt	-	5.0	-	V/µs	

## Voltage Current Characteristic of SCR

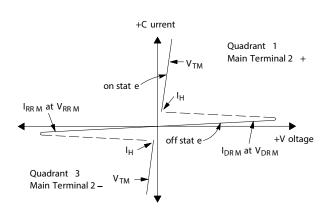
Symbol	Parameter				
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage				
I	Peak Forward Blocking Current				
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage				
I <sub>RRM</sub>	Peak Reverse Blocking Current				
V <sub>TM</sub>	Maximum On State Voltage				
I <sub>H</sub>	Holding Current				





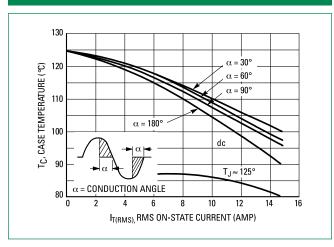
All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used

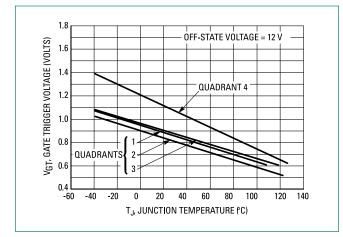




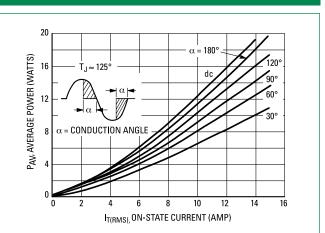
#### Figure 1. RMS Current Derating



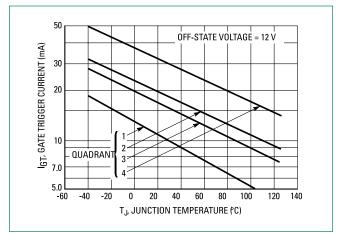
#### Figure 3. Typical Gate Trigger Voltage



#### Figure 2. On–State Power Dissipation

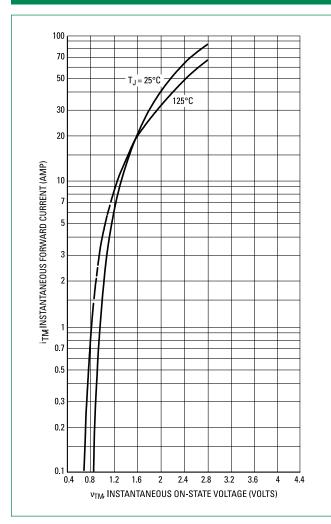


#### Figure 4. Typical Gate Trigger Current

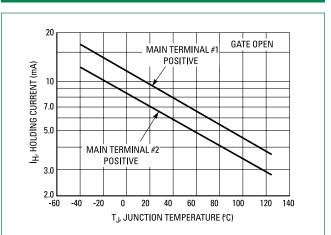




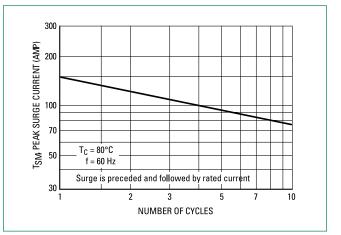
## Figure 5. On–State Characteristics



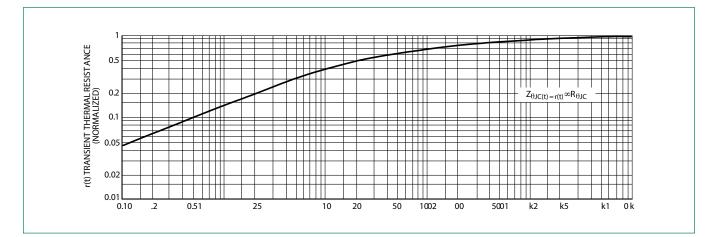
## Figure 6. Typical Holding Current



## Figure 7. Maximum Non–Repetitive Surge Current



## Figure 8. Thermal Response

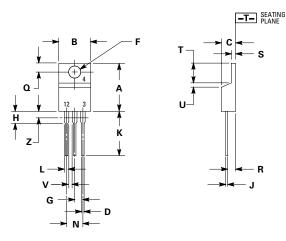




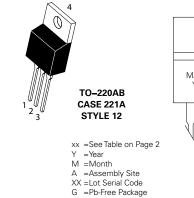
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#### **Dimensions**



## Part Marking System





Dim	Inc	hes	Millin	neters
Dim	Min	Мах	Min	Мах
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
К	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
Ν	0.195	0.205	4.95	5.21
٥	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
v	0.045		1.15	
Z		0.080		2.04

Pin Assignment			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	No Connection		
	h		

Ordering Information					
Device	Device Marking	Package	Shipping		
MAC15-8G	MAC15-8				
MAC15-10G	MAC1510				
MAC15A6G	MAC15A6	TO-220AB (Pb-Free)	500 Units/Box		
MAC15A8G	MAC15A8				
MAC15A10G	MAC15A10				

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

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